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### **LPC662**

## Low Power CMOS Dual Operational Amplifier

### **General Description**

The LPC662 CMOS Dual operational amplifier is ideal for operation from a single supply. It features a wide range of operating voltage from +5V to +15V, rail-to-rail output swing in addition to an input common-mode range that includes ground. Performance limitations that have plagued CMOS amplifiers in the past are not a problem with this design. Input  $V_{\rm OS}$ , drift, and broadband noise as well as voltage gain (into 100 k $\Omega$  and 5 k $\Omega$ ) are all equal to or better than widely accepted bipolar equivalents, while the power supply requirement is typically less than 0.5 mW.

This chip is built with National's advanced Double-Poly Silicon-Gate CMOS process.

See the LPC660 datasheet for a Quad CMOS operational amplifier and LPC661 for a single CMOS operational amplifier with these same features.

### **Applications**

- High-impedance buffer
- Precision current-to-voltage converter

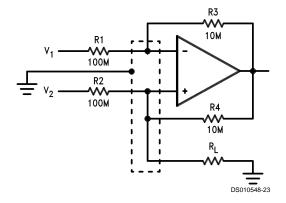
- Long-term integrator
- High-impedance preamplifier
- Active filter
- Sample-and-Hold circuit
- Peak detector

#### **Features**

- Rail-to-rail output swing
- Micropower operation (<0.5 mW)</p>
- Specified for 100 kΩ and 5 kΩ loads
- High voltage gain
   Low input offset voltage
   Low offset voltage drift
   120 dB
   3 mV
   Low offset voltage drift
   1.3 µV/°C
- Ultra low input bias current
- Input common-mode includes GNDOperating range from +5V to +15V
- Low distortion 0.01% at 1 kHz
   Slew rate 0.11 V/µs
- Full military temperature range available

## **Application Circuit**

#### **Howland Current Pump**



### **Absolute Maximum Ratings** (Note 3)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Differential Input Voltage  $\pm$ Supply Voltage Supply Voltage (V<sup>+</sup> – V<sup>-</sup>) 16V Output Short Circuit to V<sup>+</sup> (Note 11) Output Short Circuit to V<sup>-</sup> (Note 1) Lead Temperature

Storage Temp. Range  $-65^{\circ}\text{C}$  to  $+150^{\circ}\text{C}$  Junction Temperature  $150^{\circ}\text{C}$ 

ESD Rating

(Soldering, 10 sec.)

 $\begin{array}{ll} \text{(C = 100 pF, R = 1.5 k}\Omega) & \text{1000V} \\ \text{Power Dissipation} & \text{(Note 2)} \\ \text{Current at Input Pin} & \pm 5 \text{ mA} \\ \end{array}$ 

Current at Output Pin ±18 mA

Current at Power Supply Pin 35 mA Voltage at Input/Output Pin  $(V^+)$  + 0.3V,  $(V^-)$  -0.3V

### **Operating Ratings** (Note 3)

Temperature Range

Thermal Resistance  $(\theta_{JA})$  (Note 10)

 8-Pin Ceramic DIP
 100°C/W

 8-Pin Molded DIP
 101°C/W

 8-Pin SO
 165°C/W

 8-Pin Side Brazed Ceramic DIP
 100°C/W

### **DC Electrical Characteristics**

Unless otherwise specified, all limits guaranteed for  $T_J = 25$  °C. **Boldface** limits apply at the temperature extremes.  $V^+ = 5V$ ,  $V^- = 0V$ ,  $V_{CM} = 1.5V$ ,  $V_O = 2.5V$  and  $R_L > 1M$  unless otherwise specified.

260°C

Parameter	Conditions	Тур	LPC662AM LPC662AMJ/883 Limit	LPC662AI Limit (Note 4)	LPC662I Limit (Note 4)	Units
			(Notes 4, 8)	(1010-1)	(1.1010 1)	
Input Offset Voltage		1	3	3	6	mV
			3.5	3.3	6.3	max
Input Offset Voltage		1.3				μV/°C
Average Drift						
Input Bias Current		0.002	20			pА
			100	4	4	max
Input Offset Current		0.001	20			pA
			100	2	2	max
Input Resistance		>1				Tera Ω
Common Mode	$0V \le V_{CM} \le 12.0V$	83	70	70	63	dB
Rejection Ratio	V <sup>+</sup> = 15V		68	68	61	min
Positive Power Supply	5V ≤ V <sup>+</sup> ≤ 15V	83	70	70	63	dB
Rejection Ratio	$V_{O} = 2.5V$		68	68	61	min
Negative Power Supply	0V ≤ V <sup>-</sup> ≤ −10V	94	84	84	74	dB
Rejection Ratio			82	83	73	min
Input Common-Mode	V <sup>+</sup> = 5V and 15V	-0.4	-0.1	-0.1	-0.1	V
Voltage Range	For CMRR ≥ 50 dB		0	0	0	max
		V+ - 1.9	V+ - 2.3	V+ - 2.3	V+ - 2.3	V
			V <sup>+</sup> - 2.6	V <sup>+</sup> - 2.5	V <sup>+</sup> - 2.5	min
Large Signal	$R_L = 100 \text{ k}\Omega \text{ (Note 5)}$	1000	400	400	300	V/mV
Voltage Gain	Sourcing		250	300	200	min
	Sinking	500	180	180	90	V/mV
			70	120	70	min
	$R_L = 5 \text{ k}\Omega \text{ (Note 5)}$	1000	200	200	100	V/mV
	Sourcing		150	160	80	min
	Sinking	250	100	100	50	V/mV
			35	60	40	min

## **DC Electrical Characteristics** (Continued)

Unless otherwise specified, all limits guaranteed for  $T_J = 25^{\circ}C$ . **Boldface** limits apply at the temperature extremes.  $V^+ = 5V$ ,  $V^- = 0V$ ,  $V_{CM} = 1.5V$ ,  $V_O = 2.5V$  and  $R_L > 1M$  unless otherwise specified.

			LPC662AM	LPC662AI	LPC662I	
Parameter	Conditions	Тур	LPC662AMJ/883	Limit	Limit	Units
			Limit	(Note 4)	(Note 4)	
			(Notes 4, 8)			
Output Swing	V <sup>+</sup> = 5V	4.987	4.970	4.970	4.940	V
	$R_{L} = 100 \text{ k}\Omega \text{ to V}^{+}/2$		4.950	4.950	4.910	min
		0.004	0.030	0.030	0.060	V
			0.050	0.050	0.090	max
	V <sup>+</sup> = 5V	4.940	4.850	4.850	4.750	V
	$R_L = 5 \text{ k}\Omega \text{ to V}^+/2$		4.750	4.750	4.650	min
		0.040	0.150	0.150	0.250	V
			0.250	0.250	0.350	max
	V <sup>+</sup> = 15V	14.970	14.920	14.920	14.880	V
	$R_L = 100 \text{ k}\Omega \text{ to V}^+/2$		14.880	14.880	14.820	min
		0.007	0.030	0.030	0.060	V
			0.050	0.050	0.090	max
	V <sup>+</sup> = 15V	14.840	14.680	14.680	14.580	V
	$R_L = 5 k\Omega \text{ to V}^+/2$		14.600	14.600	14.480	min
		0.110	0.220	0.220	0.320	V
			0.300	0.300	0.400	max
Output Current	Sourcing, V <sub>O</sub> = 0V	22	16	16	13	mA
$V^{+} = 5V$			12	14	11	min
	Sinking, V <sub>O</sub> = 5V	21	16	16	13	mA
			12	14	11	min
Output Current	Sourcing, V <sub>O</sub> = 0V	40	19	28	23	mA
$V^{+} = 15V$			19	25	20	min
	Sinking, V <sub>O</sub> = 13V	39	19	28	23	mA
	(Note 11)		19	24	19	min
Supply Current	Both Amplifiers	86	120	120	140	μA
	$V_{O} = 1.5V$		145	140	160	max

### **AC Electrical Characteristics**

Unless otherwise specified, all limits guaranteed for  $T_J = 25^{\circ}\text{C}$ . **Boldface** limits apply at the temperature extremes.  $V^+ = 5V$ ,  $V^- = 0V$ ,  $V_{CM} = 1.5V$ ,  $V_O = 2.5V$  and  $R_L > 1M$  unless otherwise specified.

			LPC662AM	LPC662AI	LPC662I	
Parameter	Conditions	Тур	LPC662AMJ/883	Limit	Limit	Units
			Limit	(Note 4)	(Note 4)	
			(Notes 4, 8)			
Slew Rate	(Note 6)	0.11	0.07	0.07	0.05	V/µs
			0.04	0.05	0.03	min
Gain-Bandwidth Product		0.35				MHz
Phase Margin		50				Deg
Gain Margin		17				dB
Amp-to-Amp Isolation	(Note 7)	130				dB
Input Referred Voltage Noise	F = 1 kHz	42				nV/√Hz
Input Referred Current Noise	F = 1 kHz	0.0002				pA/√Hz
Total Harmonic Distortion	$F = 1 \text{ kHz}, A_V = -10, V^+ = 15V$	0.01				%
	$R_L = 100 \text{ k}\Omega, V_O = 8 V_{PP}$					

Note 1: Applies to both single supply and split supply operation. Continuous short circuit operation at elevated ambient temperature and/or multiple Op Amp shorts can result in exceeding the maximum allowed junction temperature of 150°C. Output currents in excess of ±30 mA over long term may adversely affect reliability.

Note 2: The maximum power dissipation is a function of  $T_{J(max)}$ ,  $\theta_{JA}$ , and  $T_A$ . The maximum allowable power dissipation of any ambient temperature is  $P_D = (T_{J(max)} - T_A)/\theta_{JA}$ .

**Note 3:** Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed.

Note 4: Limits are guaranteed by testing or correlation.

Note 5:  $V^+ = 15V$ ,  $V_{CM} = 7.5V$  and  $R_L$  connected to 7.5V. For Sourcing tests,  $7.5V \le V_O \le 11.5V$ . For Sinking tests,  $2.5V \le V_O \le 7.5V$ .

Note 6: V<sup>+</sup> = 15V. Connected as Voltage Follower with 10V step input. Number specified is the slower of the positive and negative slew rates.

Note 7: Input referred. V<sup>+</sup> = 15V and R<sub>L</sub> = 100 k $\Omega$  connected to V<sup>+</sup>/2. Each amp excited in turn with 1 kHz to produce V<sub>O</sub> = 13 V<sub>PP</sub>.

Note 8: A military RETS electrical test specification is available on request. At the time of printing, the LPC662AMJ/883 RETS specification complied fully with the boldface limits in this column. The LPC662AMJ/883 may also be procured to a Standard Military Drawing specification.

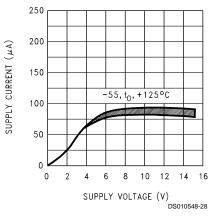
Note 9: For operating at elevated temperatures the device must be derated based on the thermal resistance  $\theta_{JA}$  with  $P_D = (T_J - T_A)/\theta_{JA}$ .

Note 10: All numbers apply for packages soldered directly into a PC board.

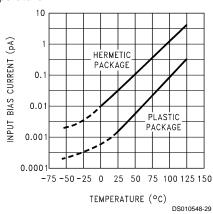
Note 11: Do not connect output to V+when V+ is greater than 13V or reliability may be adversely affected.

# Typical Performance Characteristics $V_S = \pm 7.5V$ , $T_A = 25^{\circ}C$ unless otherwise specified

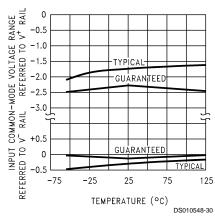
#### Supply Current vs Supply Voltage



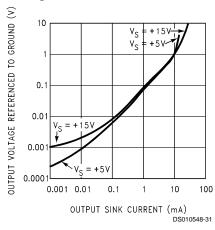
# Input Bias Current vs Temperature



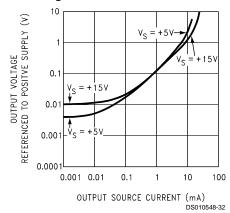
#### Input Common-Mode Voltage Range vs Temperature



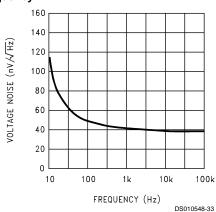
#### Output Characteristics Current Sinking



# Output Characteristics Current Sourcing

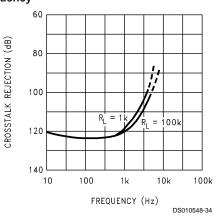


# Input Voltage Noise vs Frequency

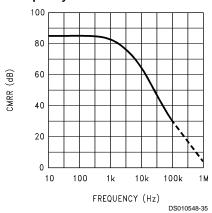


## Typical Performance Characteristics $V_S = \pm 7.5 V$ , $T_A = 25^{\circ} C$ unless otherwise specified (Continued)

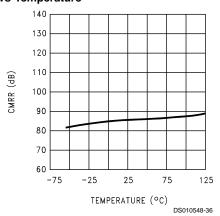
# Crosstalk Rejection vs Frequency



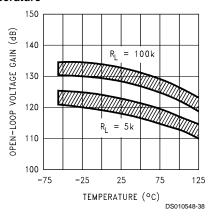
#### **CMRR** vs Frequency



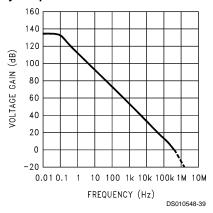
#### **CMRR** vs Temperature



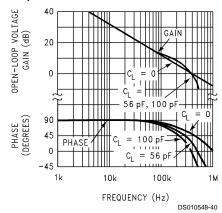
# Open-Loop Voltage Gain vs Temperature



#### Open-Loop Frequency Response

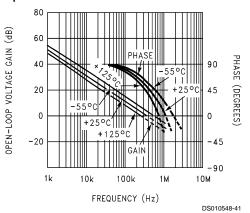


# Gain and Phase Responses vs Load Capacitance

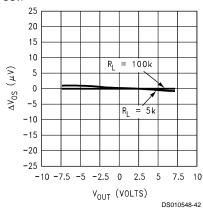


# Typical Performance Characteristics $V_S = \pm 7.5V$ , $T_A = 25^{\circ}C$ unless otherwise specified (Continued)

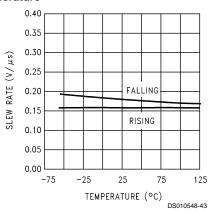
# Gain and Phase Responses vs Temperature



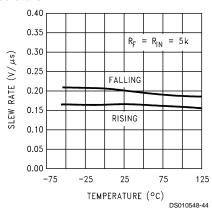
### Gain Error (V<sub>OS</sub>vs V<sub>OUT</sub>)



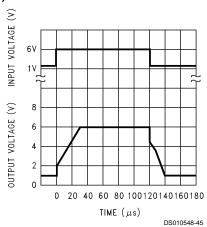
# Non-Inverting Slew Rate vs Temperature



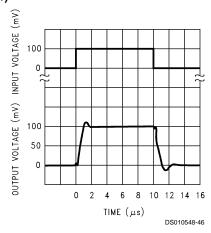
# Inverting Slew Rate vs Temperature



#### Large-Signal Pulse Non-Inverting Response (A<sub>V</sub> = +1)

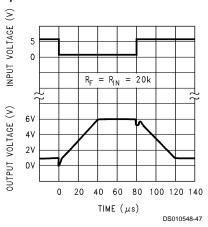


#### Non-Inverting Small Signal Pulse Response $(A_V = +1)$

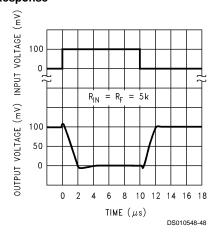


## Typical Performance Characteristics $V_S = \pm 7.5V$ , $T_A = 25^{\circ}C$ unless otherwise specified (Continued)

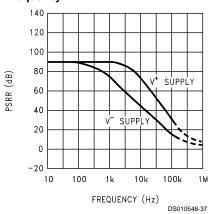
# Inverting Large-Signal Pulse Response



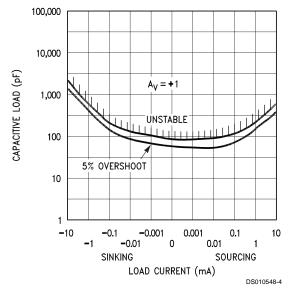
# Inverting Small-Signal Pulse Response



# Power Supply Rejection Ratio vs Frequency

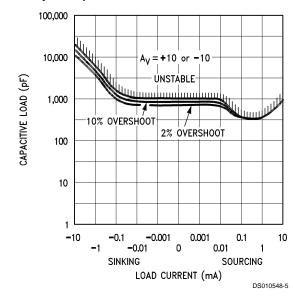


## Stability vs Capacitive Load



Note: Avoid resistive loads of less than  $500\Omega,$  as they may cause instability.

#### Stability vs Capacitive Load



### **Application Hints**

#### **AMPLIFIER TOPOLOGY**

The topology chosen for the LPC662 is unconventional (compared to general-purpose op amps) in that the traditional unity-gain buffer output stage is not used; instead, the output is taken directly from the output of the integrator, to allow rail-to-rail output swing. Since the buffer traditionally delivers the power to the load, while maintaining high op amp gain and stability, and must withstand shorts to either rail, these tasks now fall to the integrator.

As a result of these demands, the integrator is a compound affair with an embedded gain stage that is doubly fed forward (via  $C_{\rm f}$  and  $C_{\rm ff}$ ) by a dedicated unity-gain compensation driver. In addition, the output portion of the integrator is a push-pull configuration for delivering heavy loads. While sinking current the whole amplifier path consists of three gain stages with one stage fed forward, whereas while sourcing the path contains four gain stages with two fed forward.

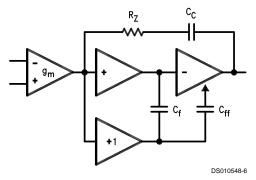


FIGURE 1. LPC662 Circuit Topology (Each Amplifier)

The large signal voltage gain while sourcing is comparable to traditional bipolar op amps for load resistance of at least 5 k $\Omega$ . The gain while sinking is higher than most CMOS op amps, due to the additional gain stage; however, when driving load resistance of 5 k $\Omega$  or less, the gain will be reduced as indicated in the Electrical Characteristics. The op amp can drive load resistance as low as 500 $\Omega$  without instability.

#### **COMPENSATING INPUT CAPACITANCE**

Refer to the LMC660 or LMC662 datasheets to determine whether or not a feedback capacitor will be necessary for compensation and what the value of that capacitor would be.

#### **CAPACITIVE LOAD TOLERANCE**

Like many other op amps, the LPC662 may oscillate when its applied load appears capacitive. The threshold of oscillation varies both with load and circuit gain. The configuration most sensitive to oscillation is a unity-gain follower. See the Typical Performance Characteristics.

The load capacitance interacts with the op amp's output resistance to create an additional pole. If this pole frequency is sufficiently low, it will degrade the op amp's phase margin so that the amplifier is no longer stable at low gains. The addition of a small resistor ( $50\Omega$  to  $100\Omega$ ) in series with the op amp's output, and a capacitor (5 pF to 10 pF) from inverting input to output pins, returns the phase margin to a safe value without interfering with lower-frequency circuit operation. Thus, larger values of capacitance can be

tolerated without oscillation. Note that in all cases, the output will ring heavily when the load capacitance is near the threshold for oscillation.

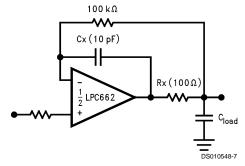


FIGURE 2. Rx, Cx Improve Capacitive Load Tolerance

Capacitive load driving capability is enhanced by using a pull up resistor to V\* Figure 3. Typically a pull up resistor conducting 50  $\,\mu A$  or more will significantly improve capacitive load responses. The value of the pull up resistor must be determined based on the current sinking capability of the amplifier with respect to the desired output swing. Open loop gain of the amplifier can also be affected by the pull up resistor (see Electrical Characteristics).

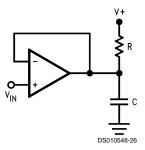


FIGURE 3. Compensating for Large Capacitive Loads with A Pull Up Resistor

# PRINTED-CIRCUIT-BOARD LAYOUT FOR HIGH-IMPEDANCE WORK

It is generally recognized that any circuit which must operate with less than 1000 pA of leakage current requires special layout of the PC board. When one wishes to take advantage of the ultra-low bias current of the LPC662, typically less than 0.04 pA, it is essential to have an excellent layout. Fortunately, the techniques for obtaining low leakages are quite simple. First, the user must not ignore the surface leakage of the PC board, even though it may sometimes appear acceptably low, because under conditions of high humidity or dust or contamination, the surface leakage will be appreciable.

To minimize the effect of any surface leakage, lay out a ring of foil completely surrounding the LPC662's inputs and the terminals of capacitors, diodes, conductors, resistors, relay terminals, etc. connected to the op-amp's inputs. See *Figure 4*. To have a significant effect, guard rings should be placed on both the top and bottom of the PC board. This PC foil must then be connected to a voltage which is at the same voltage as the amplifier inputs, since no leakage current can flow between two points at the same potential. For example, a PC board trace-to-pad resistance of 10<sup>12</sup> ohms, which is normally considered a very large resistance, could leak 5 pA if the trace were a 5V bus adjacent to the pad of an input.

9

### **Application Hints** (Continued)

This would cause a 100 times degradation from the LPC662's actual performance. However, if a guard ring is held within 5 mV of the inputs, then even a resistance of 10<sup>11</sup> ohms would cause only 0.05 pA of leakage current, or perhaps a minor (2:1) degradation of the amplifier's

performance. See *Figure 5a*, *Figure 5b*, *Figure 5c* for typical connections of guard rings for standard op-amp configurations. If both inputs are active and at high impedance, the guard can be tied to ground and still provide some protection; see *Figure 5d*.

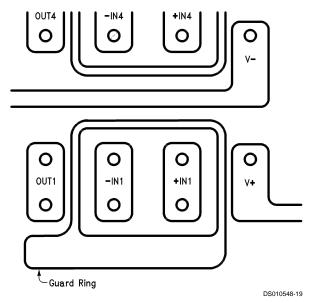


FIGURE 4. Example of Guard Ring in P.C. Board Layout, using the LPC660

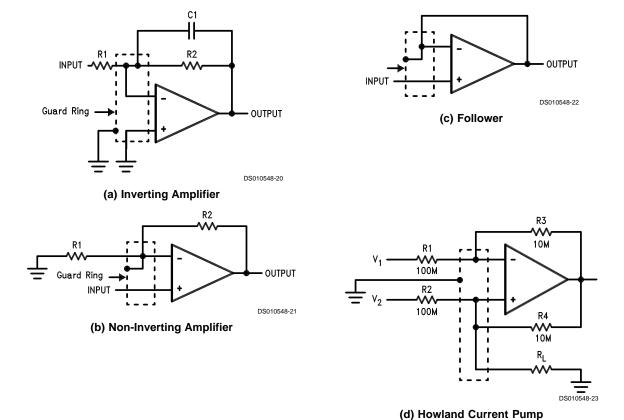


FIGURE 5. Guard Ring Connections

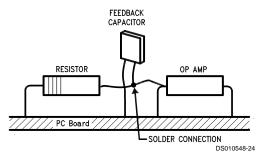
to lay out a PC board for the sake of just a few circuits, there

The designer should be aware that when it is inappropriate

is another technique which is even better than a guard ring on a PC board: Don't insert the amplifier's input pin into the

### **Application Hints** (Continued)

board at all, but bend it up in the air and use only air as an insulator. Air is an excellent insulator. In this case you may have to forego some of the advantages of PC board construction, but the advantages are sometimes well worth the effort of using point-to-point up-in-the-air wiring. See *Figure 6*.



(Input pins are lifted out of PC board and soldered directly to components. All other pins connected to PC board.)

#### FIGURE 6. Air Wiring

#### **BIAS CURRENT TESTING**

The test method of *Figure 7* is appropriate for bench-testing bias current with reasonable accuracy. To understand its operation, first close switch S2 momentarily. When S2 is opened, then

$$I^{-} = \frac{dV_{OUT}}{dt} \times C2.$$

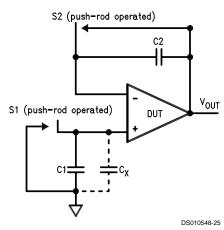


FIGURE 7. Simple Input Bias Current Test Circuit

A suitable capacitor for C2 would be a 5 pF or 10 pF silver mica, NPO ceramic, or air-dielectric. When determining the magnitude of  $I^-$ , the leakage of the capacitor and socket must be taken into account. Switch S2 should be left shorted most of the time, or else the dielectric absorption of the capacitor C2 could cause errors.

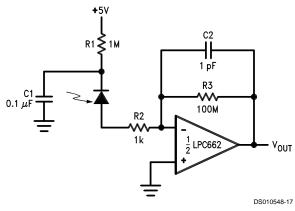
Similarly, if S1 is shorted momentarily (while leaving S2 shorted)  $\,$ 

$$I^{+} = \frac{dV_{OUT}}{dt} \times (C1 + C_{x})$$

where C<sub>x</sub> is the stray capacitance at the + input.

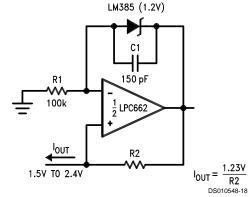
## **Typical Single-Supply Applications** $(V^+ = 5.0 V_{DC})$

#### **Photodiode Current-to-Voltage Converter**



**Note:** A 5V bias on the photodiode can cut its capacitance by a factor of 2 or 3, leading to improved response and lower noise. However, this bias on the photodiode will cause photodiode leakage (also known as its dark current).

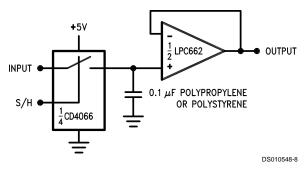
#### **Micropower Current Source**



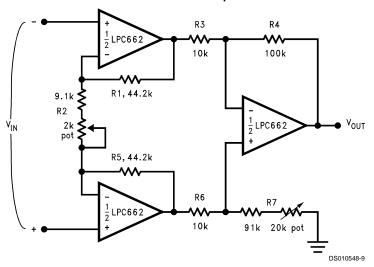
**Note:** (Upper limit of output range dictated by input common-mode range; lower limit dictated by minimum current requirement of LM385.)

## **Typical Single-Supply Applications** $(V^+ = 5.0 V_{DC})$ (Continued)

#### Low-Leakage Sample-and-Hold



#### Instrumentation Amplifier



If R1 = R5, R3 = R6 and R4 = R7; then

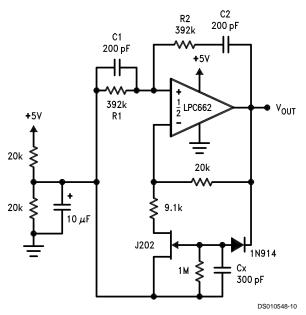
$$\frac{V_{OUT}}{V_{IN}} = \frac{R2\,+\,2R1}{R2} \times \frac{R4}{R3}$$

 $\therefore A_V \approx 100$  for circuit shown.

For good CMRR over temperature, low drift resistors should be used. Matching of R3 to R6 and R4 to R7 affects CMRR. Gain may be adjusted through R2. CMRR may be adjusted through R7.

## **Typical Single-Supply Applications** $(V^+ = 5.0 V_{DC})$ (Continued)

#### Sine-Wave Oscillator



Oscillator frequency is determined by R1, R2, C1, and C2:

 $f_{OSC} = 1/2\pi RC$ 

where R = R1 = R2 and C = C1 = C2.

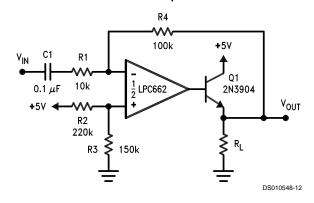
This circuit, as shown, oscillates at 2.0 kHz with a peak-to-peak output swing of 4.5V

DS010548-11

#### 1 Hz Square-Wave Oscillator

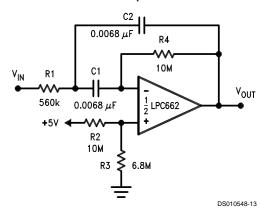
## 10M 10M Vout 10M Vout 470k 83 470k

#### **Power Amplifier**



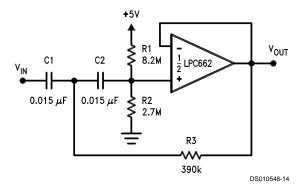
## Typical Single-Supply Applications ( $V^+ = 5.0 V_{DC}$ ) (Continued)

#### 10 Hz Bandpass Filter



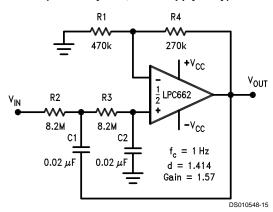
 $f_{O} = 10 \text{ Hz}$  Q = 2.1Gain = -8.8

#### 10 Hz High-Pass Filter (2 dB Dip)

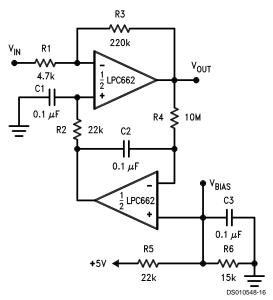


 $f_c = 10 \text{ Hz}$ d = 0.895Gain = 1

#### 1 Hz Low-Pass Filter (Maximally Flat, Dual Supply Only)



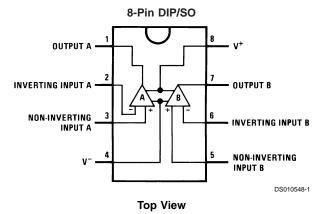
### High Gain Amplifier with Offset Voltage Reduction



Gain = -46.8

Output offset voltage reduced to the level of the input offset voltage of the bottom amplifier (typically 1 mV), referred to  $V_{BIAS}$ .

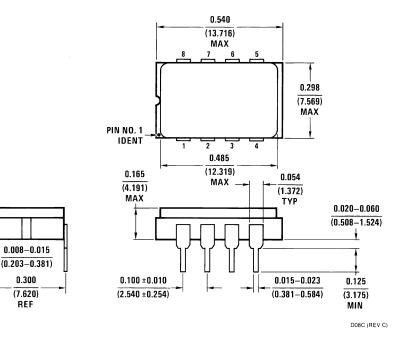
# **Connection Diagram**



# **Ordering Information**

Package	Temperatu	re Range	NSC	Transport
	Military	Industrial	Drawing	Media
8-Pin	LPC662AMD		D08C	Rail
Side Brazed				
Ceramic DIP				
8-Pin		LPC662AIM	M08A	Rail
Small Outline		or LPC662IM		Tape and Reel
8-Pin		LPC662AIN	N08E	Rail
Molded DIP		or LPC662IN		
8-Pin	LPC662AMJ/883		J08A	Rail
Ceramic DIP				

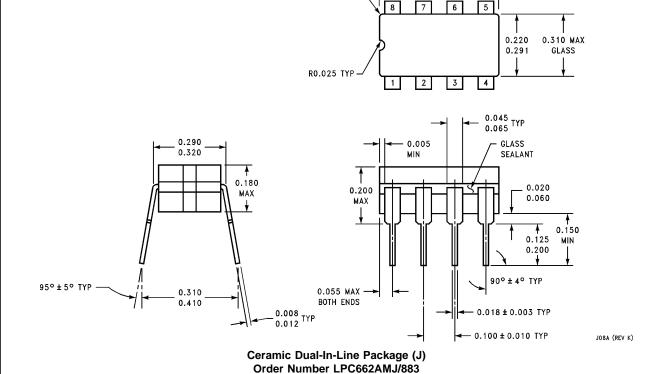
## Physical Dimensions inches (millimeters) unless otherwise noted



8-Pin Cavity Dual-In-Line Package (D) Order Number LPC662AMD NS Package Number D08C

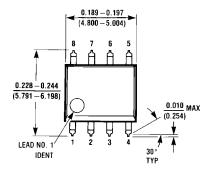
R0.010 TYP

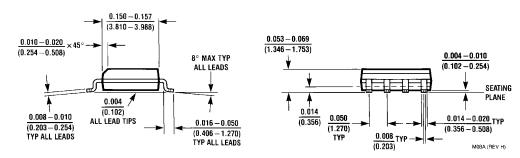
0.400 MAX



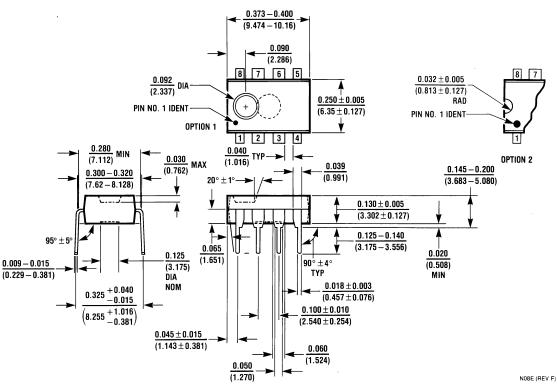
**NS Package Number J08A** 

### Physical Dimensions inches (millimeters) unless otherwise noted (Continued)





8-Pin Small Outline Molded Package (M) Order Number LPC662AIM or LPC662IM NS Package Number M08A



8-Pin Molded Dual-In-Line Package (N) Order Number LPC662AIN or LPC662IN NS Package Number N08E

### **Notes**

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**Application** 

<u>Products</u> > <u>Analog - Amplifiers</u> > <u>Operational Amplifiers</u> > <u>Low Power</u> > <u>LPC662</u>

# **LPC662 Product Folder**

## **Low Power CMOS Dual Operational Amplifier**

<u>Description</u> <u>Features</u>	<u>Datasheet</u>	& Models	<u>&amp; Pricing</u>	Tools	Notes			
Parametric Table		Parametric	Table					
Channels (Channels)	2	Maximum S	Supply Voltage (	(Volt)	15			
Input Output Type	Vcm to V-, R-R Out	Offset Volta	Offset Voltage, Max (mV)					
Bandwidth, typ (MHz)	.35	Input Bias	put Bias Current, Temp Max (nA)					
Slew Rate, typ (Volts/usec)	.11	Output Cur	Output Current, typ (mA)					
Supply Current per Channel, typ (mA)	Voltage Noi	Voltage Noise, typ (nV/Hz)						
Minimum Supply Voltage (Volt) 5 Shut down								
-	,	Special Fea	tures		-			

**Package** 

Samples

### **Datasheet**

General

Title	Size in Kbytes	Date	View Online	Download	Receive via Email
LPC662 Low Power CMOS Dual Operational Amplifier	600 Kbytes	7- Mar- 01	View Online	Download	Receive via Email
LPC662 Low Power CMOS Dual Operational Amplifier (JAPANESE)	442 Kbytes		View Online	Download	Receive via

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## Package Availability, Models, Samples & Pricing

Part Number	Pacl	kage		Status	Models		Samples &		Sampi			dgetary Pricing	Std Pack	Package Package
rait Number	Туре	Pins	MSL		SPICE	IBIS	Electronic Orders		SUS each	Size	<u>Marking</u>			
LPC662AIM	SOIC NARROW	8	MSL	Full production	LPC662A.MOD		24 Hour Buy Now	1K+	\$1.2500	rail of 95	[logo]¢2¢T LPC66 2AIM			

LPC662IM	SOIC_ NARROW	8	MSL	Full production	N/A	N/A	24 Hour Buy Now	1K+	\$0.8100	rail of 95	[logo]¢2¢T LPC66 2IM
LPC662AIMX	SOIC NARROW	8	MSL	Full production	LPC662A.MOD	N/A	Buy Now	1K+	\$1.2500	reel of 2500	[logo]¢2¢T LPC66 2AIM
LPC662IMX	SOIC NARROW	8	MSL	Full production	N/A	N/A		1K+	\$0.8100	reel of 2500	[logo]¢2¢T LPC66 2IM
LPC662AI MDC	Di	<u>le</u>		Full production	LPC662A.MOD	N/A	Samples			tray of N/A	-
LPC662I MDC	Di	<u>le</u>		Full production	N/A	N/A	Samples			tray of N/A	-
LPC662AI MWC	<u>Wa</u>	<u>fer</u>		Full production	LPC662A.MOD	N/A				wafer jar of N/A	-
LPC662I MWC	<u>Wa</u>	<u>fer</u>		Full production	N/A	N/A				wafer jar of N/A	-

### **General Description**

The LPC662 CMOS Dual operational amplifier is ideal for operation from a single supply. It features a wide range of operating voltage from +5V to +15V, rail-to-rail output swing in addition to an input common-mode range that includes ground. Performance limitations that have plagued CMOS amplifiers in the past are not a problem with this design. Input  $V_{OS}$ , drift, and broadband noise as well as voltage gain (into 100 k and 5 k) are all equal to or better than widely accepted bipolar equivalents, while the power supply requirement is typically less than 0.5 mW.

This chip is built with National's advanced Double-Poly Silicon-Gate CMOS process.

See the LPC660 datasheet for a Quad CMOS operational amplifier and LPC661 for a single CMOS operational amplifier with these same features.

#### **Features**

Rail-to-rail output swing	
Micropower operation (< 0.5 mW)	
Specified for 100 k and 5 k loads	
High voltage gain	120 dB
Low input offset voltage	3 mV
Low offset voltage drift	1.3 μV/°C
Ultra low input bias current	2 fA

Input common-mode includes GND	
Operating range from +5V to +15V	
Low distortion	0.01% at 1 kHz
Slew rate	0.11 V/μs
Full military temperature range available	

### **Applications**

- High-impedance buffer
- Precision current-to-voltage converter
- Long-term integrator
- High-impedance preamplifier
- Active filter
- Sample-and-Hold circuit
- Peak detector

### **Design Tools**

Title	Size in Kbytes	Date	Viev	w Online	Download	Receive via Email
Amplifiers Selection Guide software for Windows	7 Kbytes	12-Jun-2002	<u>View</u>	<u>/</u>		

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### **Application Notes**

Title	Size in Kbytes		View Online	Download	Receive via Email
<b>AN-856:</b> A SPICE Compatible Macromodel for CMOS Operational Amplifiers	105 Kbytes	5-Aug-95	View Online	Download	Receive via Email

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